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# Edge TCT and Charge Collection Efficiency study on pion irradiated n-on-p strips

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Silicon n-on-p strip detectors produced by CIS, have been irradiated with pions in a fluence range 2e14pi/cmˆ2-1e15pi/cmˆ2. The irradiated detectors have been measured by means of the Edge-TCT and Alibava CCE setup, as well as standard CV/IV characterization. The detectors have shown a fairly low gc value. Investigation went in the direction of looking for correlation between the different techniques, looking for a consistency, as well as determining whether measurement temperature plays a role in the obtained results.

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